

# Canary Replica Feedback for Near-DRV Standby $V_{DD}$ Scaling in a 90nm SRAM

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**CICC 2007**  
**September 17**



# Outline

- **Motivation**
- **Canary Feedback Scheme**
- **Canary Circuits Design**
- **Near-DRV  $V_{DD}$  Scaling**
- **Test Chip Implementation & Measurement**
- **Conclusion**

# Motivation – Leakage Power Reduction

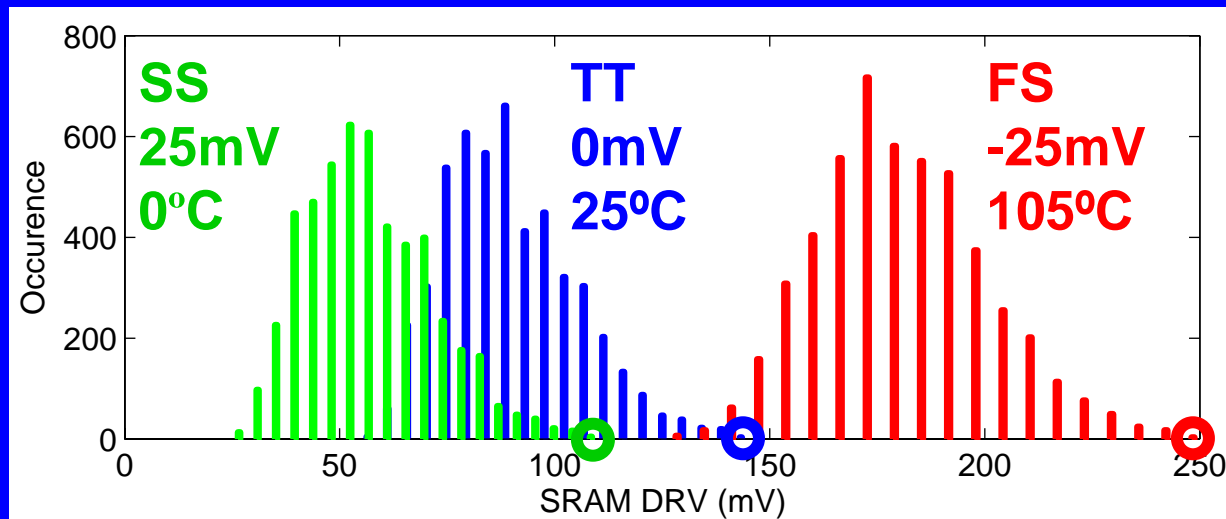
- Leakage power grows
- SRAM standby leakage power dominates
- Leakage power reduction by
  - $V_{DD}$  scaling
  - Source biasing
  - Body biasing
  - High  $V_T$  FETs
  - etc.

# Motivation – $V_{DD}$ Scaling

- SRAM hold stability is degraded
- **Data Retention Voltage (DRV):**
  - The minimum  $V_{DD}$  for preserving cell state *or*
  - The  $V_{DD}$  when Static Noise Margin (SNM) is ZERO
- Cell hold failure
  - Occurs when current  $V_{DD} < DRV$

# Motivation – DRV

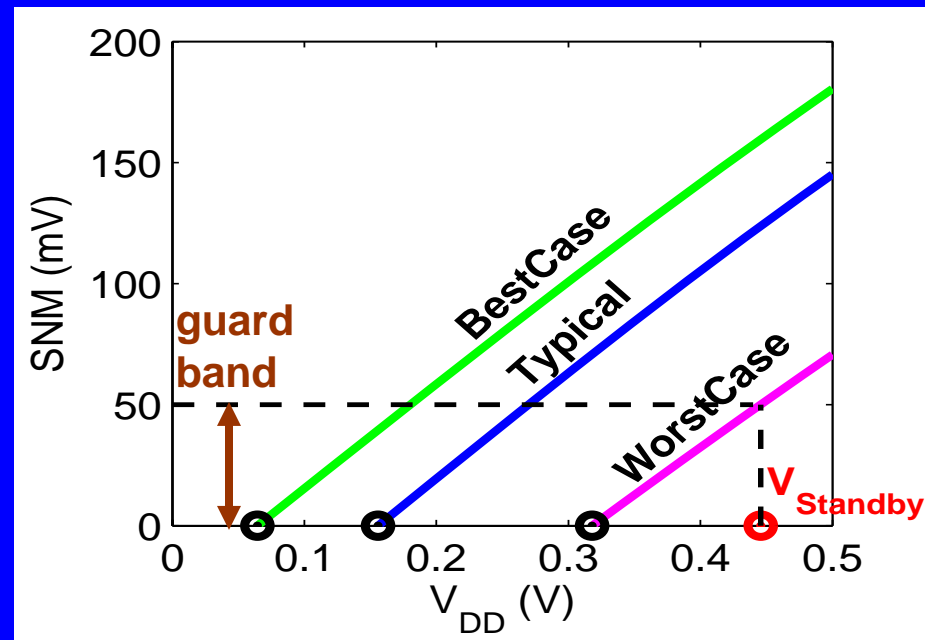
- Variability impacts DRV
- DRV of the cells is distributed
- Tail of the DRV distribution
  - Determines the  $\min(V_{DD})$  for SRAM array
  - Moves with global effects (i.e. PVT variations)



\* How to deal with the variations?

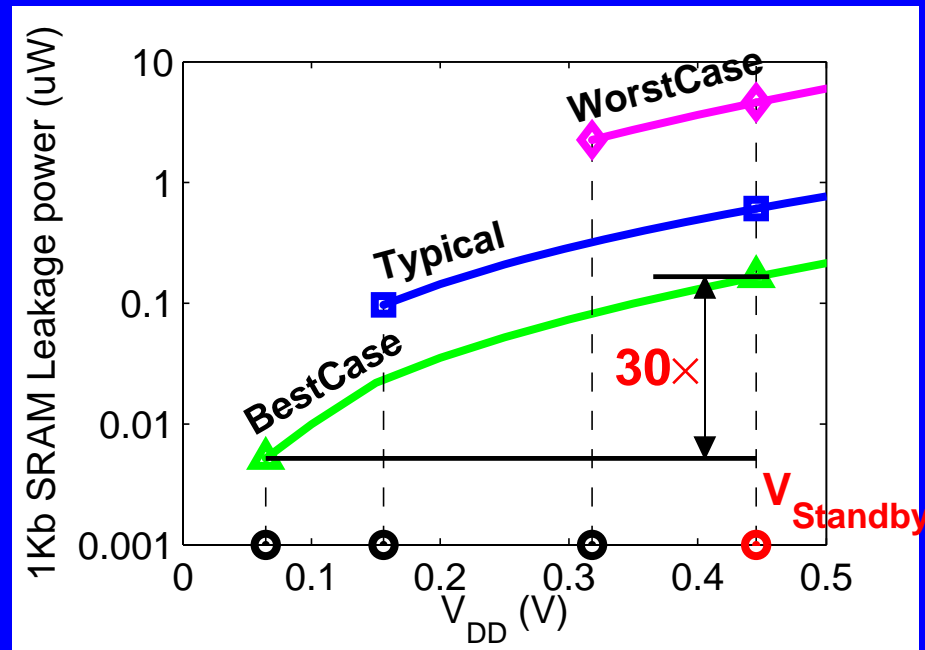
# Motivation – Worst-case Approach

- Universal standby supply voltage ( $V_{\text{standby}}$ )
  - Applied to all the dies all the time
- $V_{\text{standby}}$  determined by the stability at
  - Worst scenario *and*
  - An extra guard band (e.g. 50mV SNM)



# Motivation – Worst-case Approach

- Advantage
  - Robust
- Disadvantage
  - Limit power savings of non-worst-cases



\* Can we achieve aggressive power savings?

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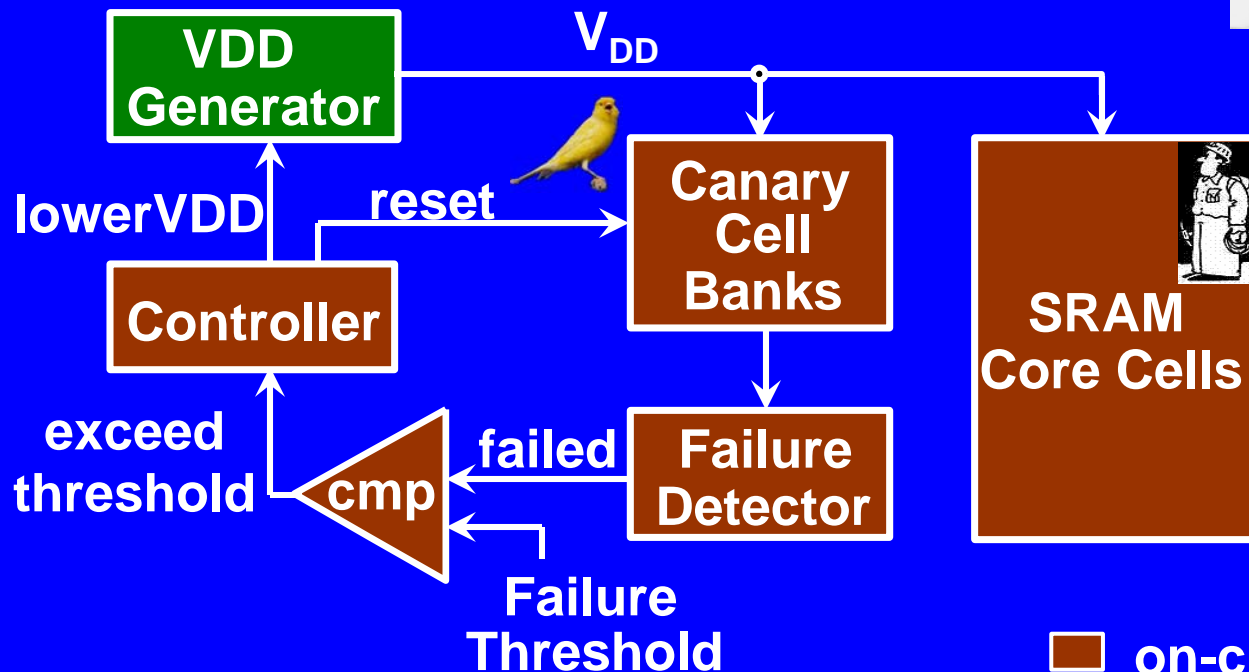


# Canary Feedback Scheme

- Use replica bitcells (canary bitcells) inspired by canary birds
- Use Canary bitcells in closed-loop  $V_{DD}$  scaling



Canary bird: warning system for coal miner

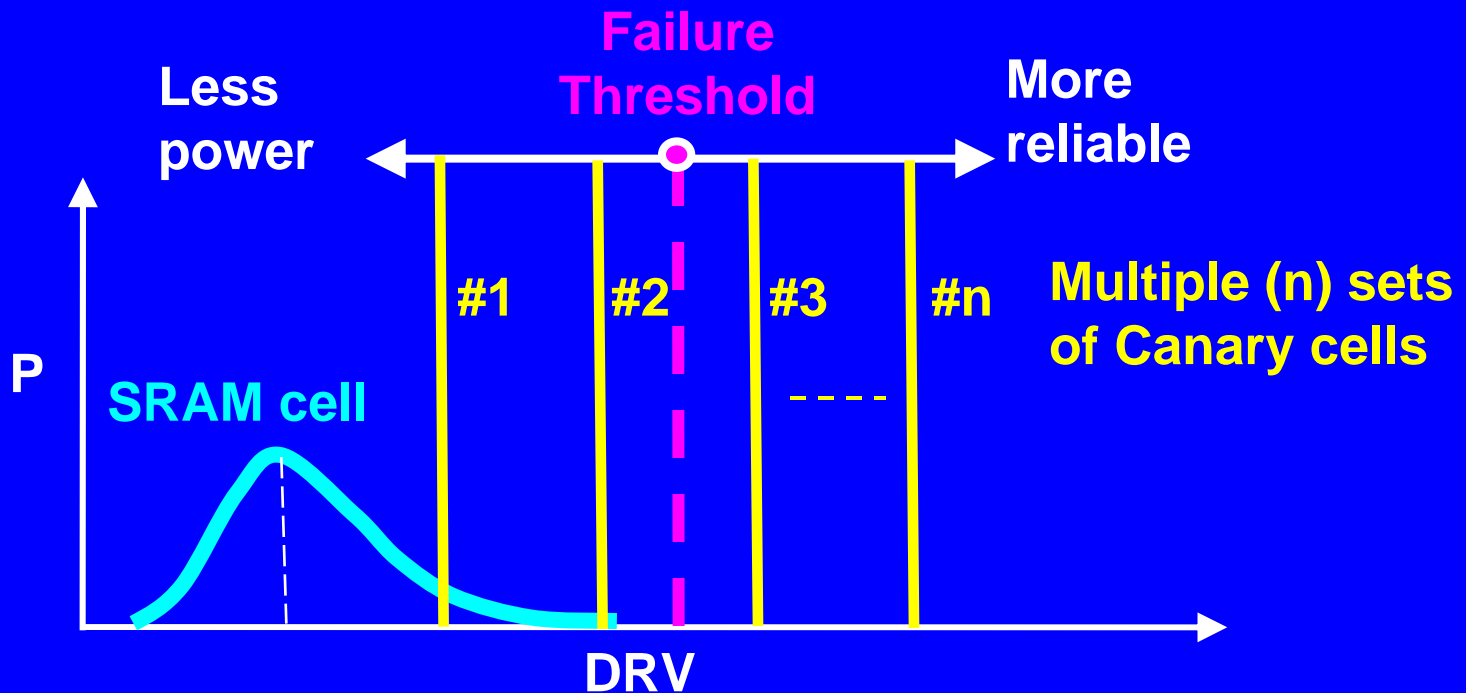


■ on-chip

■ on-chip or off-chip

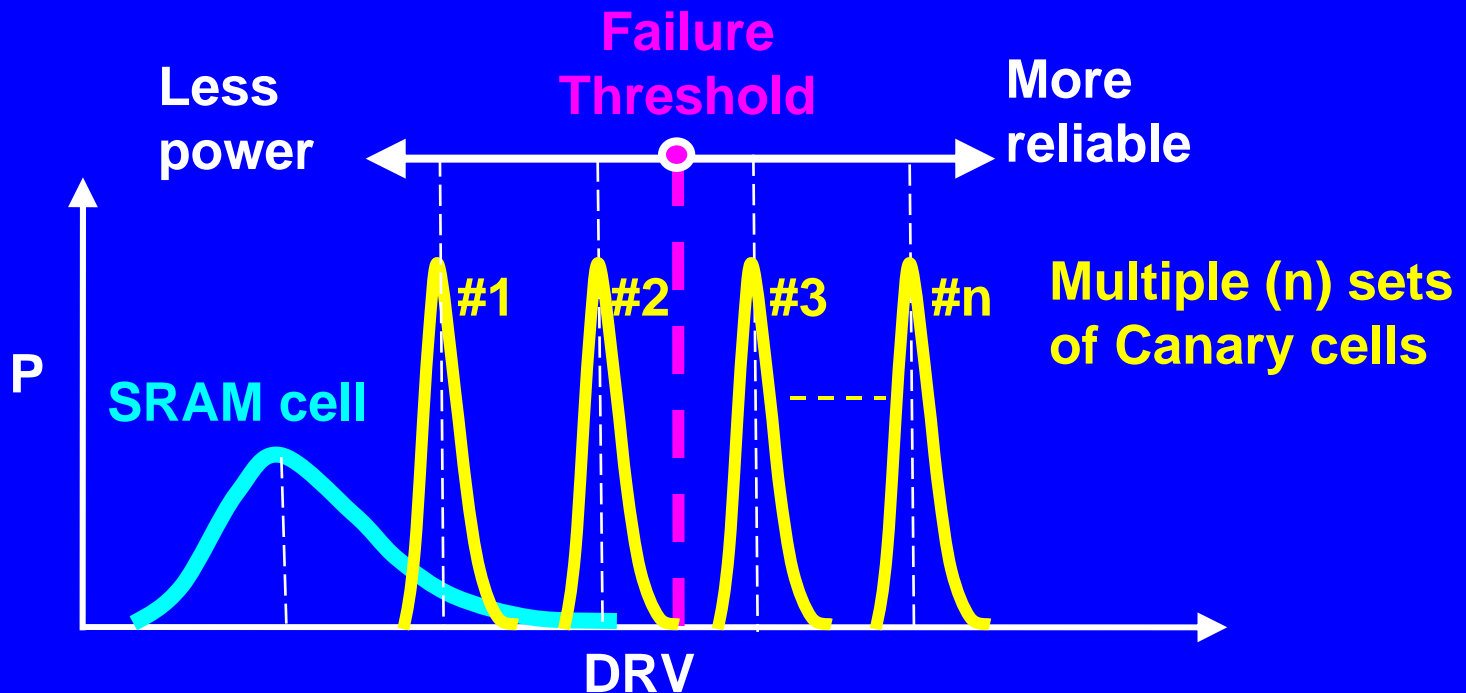
# Major Benefits

- Aggressive power savings by tracking global effects (i.e. PVT variations)
- Mechanism for tradeoff between data reliability and leakage power savings



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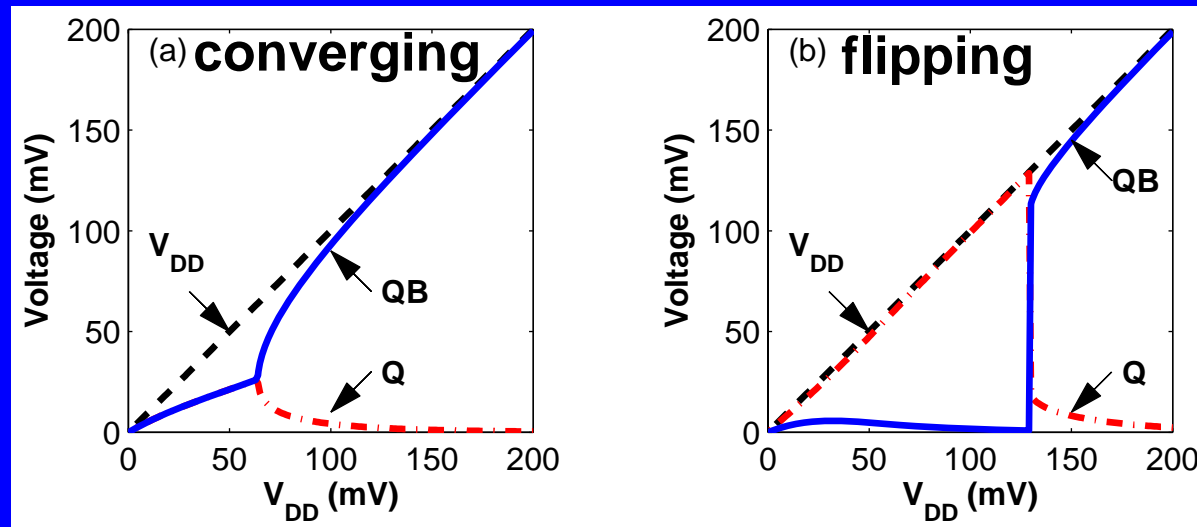
\* A higher and tunable canary DRV is essential

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# Cell Hold Failure

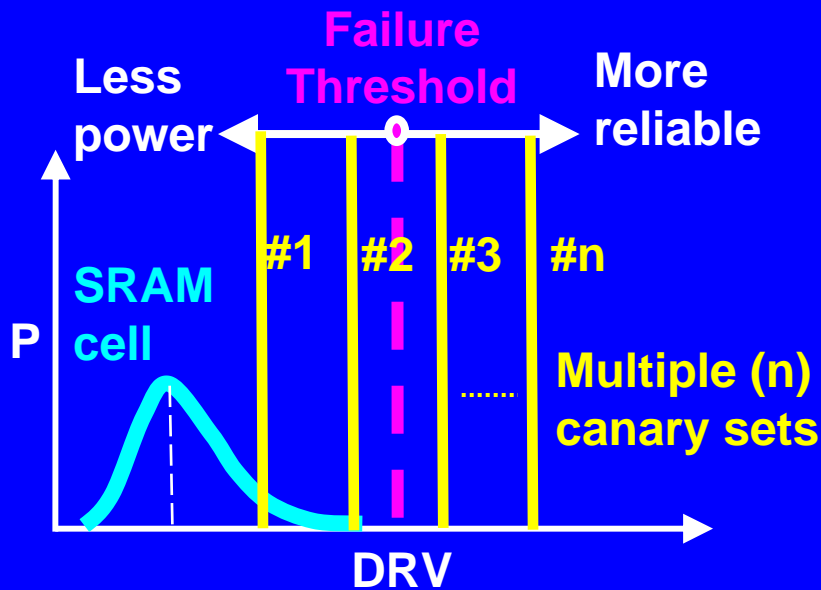
- 2 types
  - Converging failure
    - Occurs only in balanced (completely symmetrical) cells
    - Very rare under local variations
  - Flipping failure
    - Occurs in imbalanced cells



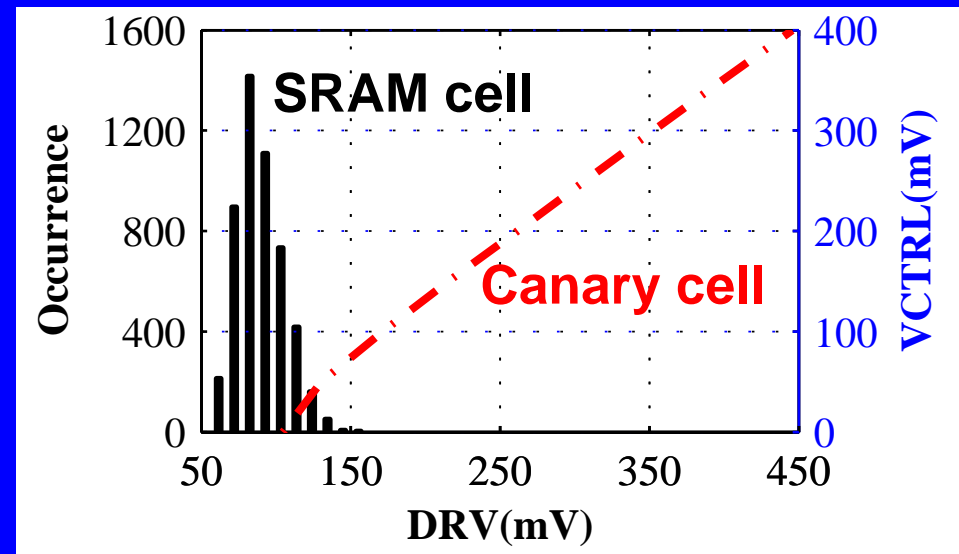


# Canary Cell

- Tunable canary DRV by
  - Altering gate voltage (**VCTRL**) of PMOS header
- Canary set with larger VCTRL has a higher DRV



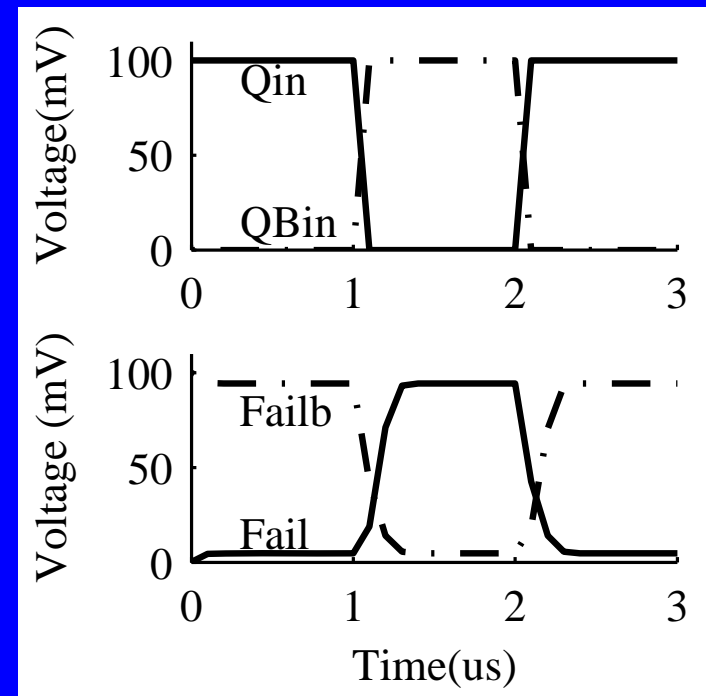
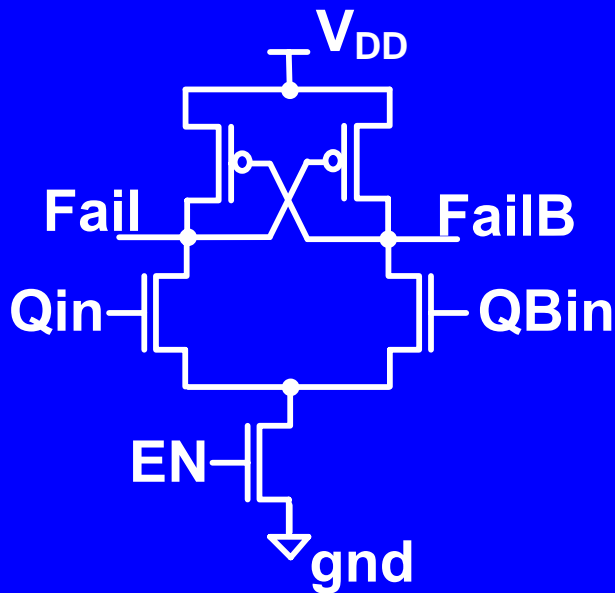
Multiple canary sets  
design concept



Simulated canary DRV vs. VCTRL  
relative to SRAM DRV  
distribution from 5-k Monte-Carlo

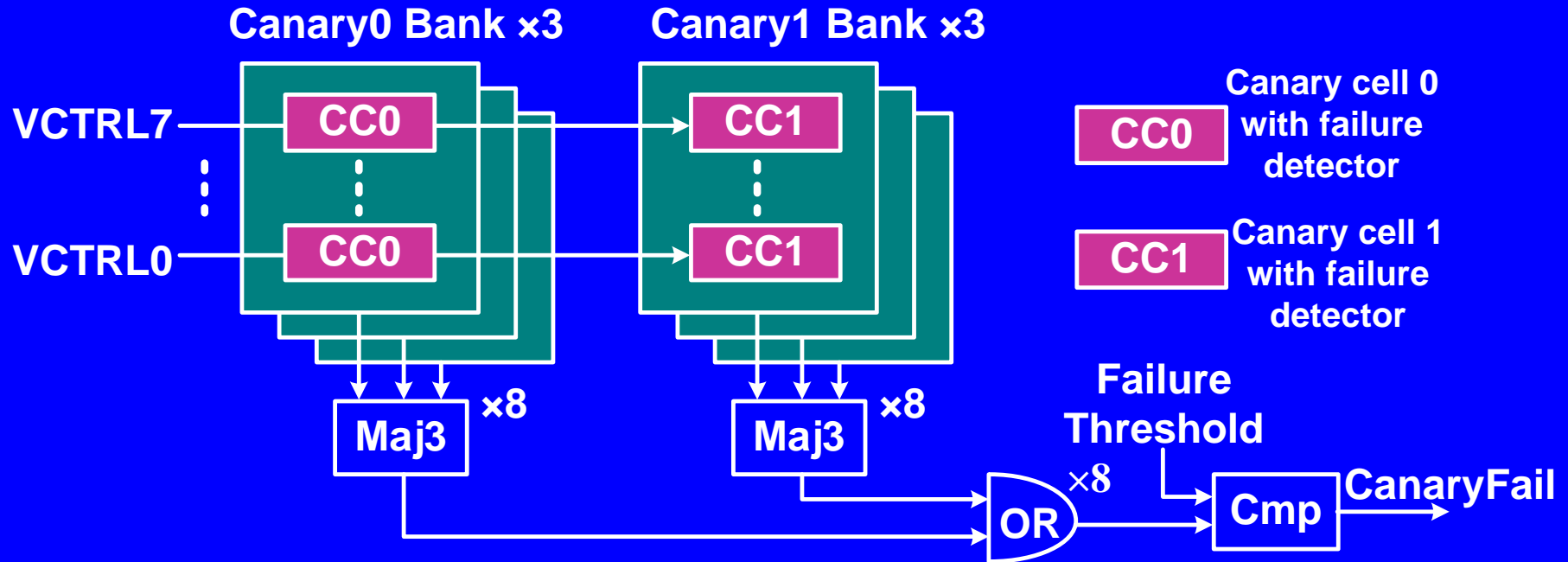
# Failure Detector

- Each canary cell connects its own failure detector
- Use sub-threshold SA to detect flipping failures





# Canary Bank

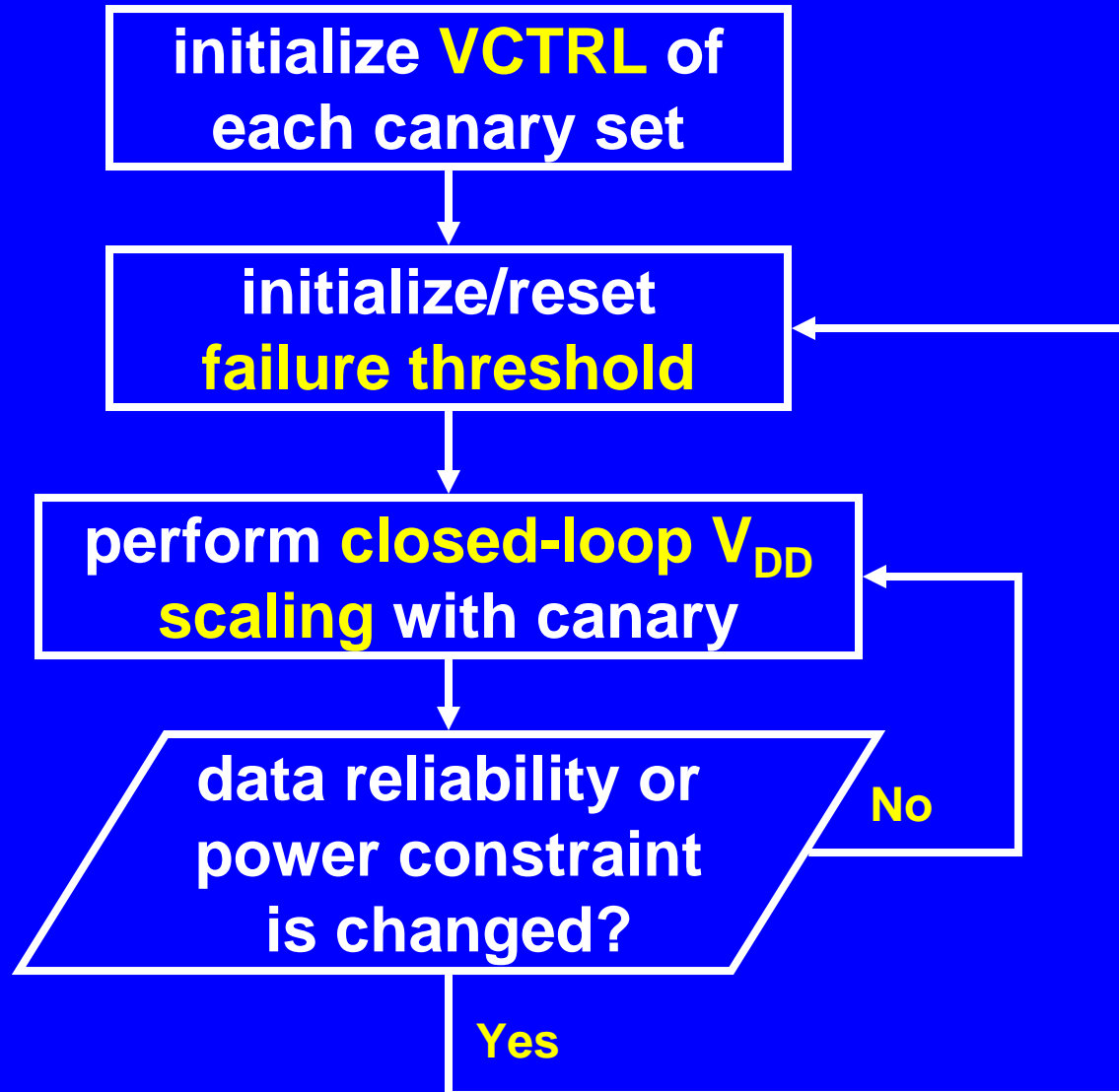


- 8 canary sets/rows with respective VCTRL
- 3-way redundancy
- OR operation on canary cell '0' and '1'
- Failure threshold comparator

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# Near-DRV $V_{DD}$ Scaling Procedures



# SRAM DRV Characterization

- Measurement at test time
  - Accurate but expensive
- Traditional Monte-Carlo (M-C) Simulation
  - Accurate but too time-consuming for large arrays
- Alternative fast methods

- A new DRV model based on SNM [1]

$$\max(DRV) = \frac{1}{k} \left( \sqrt{2}\sigma_0 \cdot \operatorname{erfc}^{-1} \left( 2 - 2\sqrt{\frac{m-1}{m}} \right) - \mu_0 \right) + V_0$$

- The Statistical Blockade tool [2]

Fast Monte-Carlo for simulating rare events

Each has <2% avg. error rate & >10<sup>4</sup>x speed-up compared with M-C [1]

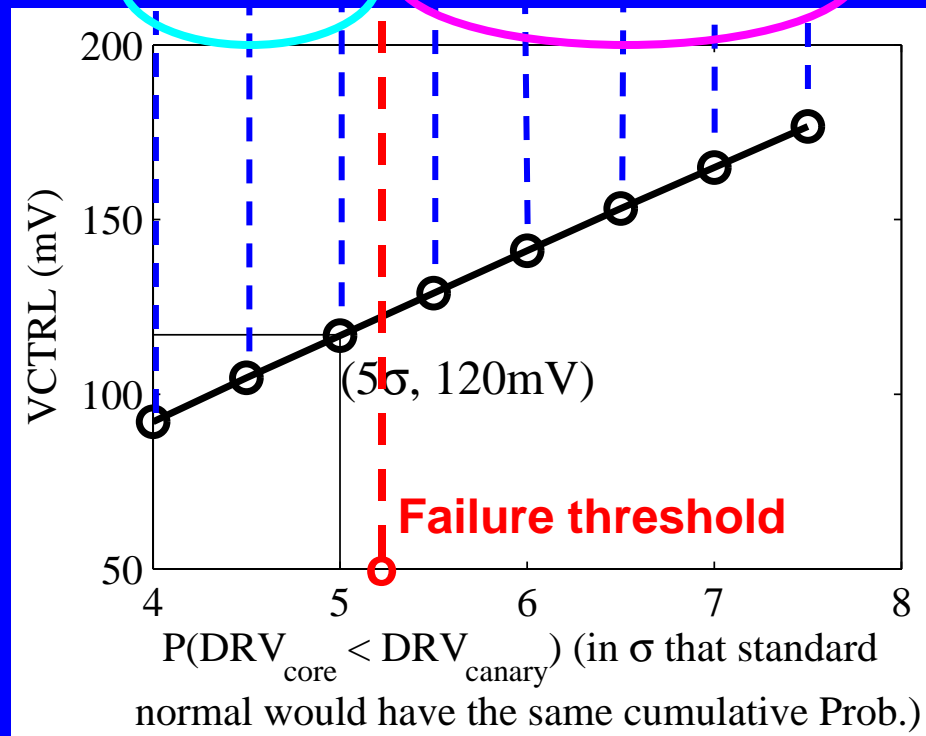
[1] J. Wang, A. Singhee, R. A. Runtenbar, and B. H. Calhoun, “Statistical Modeling the minimum standby supply voltage of a full SRAM Array”, ESSCIRC 2007.

[2] A. Singhee and R. A. Runtenbar, “Statistical Blockade: A Novel Method for Very Fast Monte Carlo Simulation of Rare Circuit Events, and Its Application”, DATE 2007.

# Canary Configuration

- Choose VCTRLs of canary sets based on
  - SRAM DRV estimation *and*
  - Linear dependency of Canary DRV on VCTRL
- Pick failure threshold based on the reliability constraint

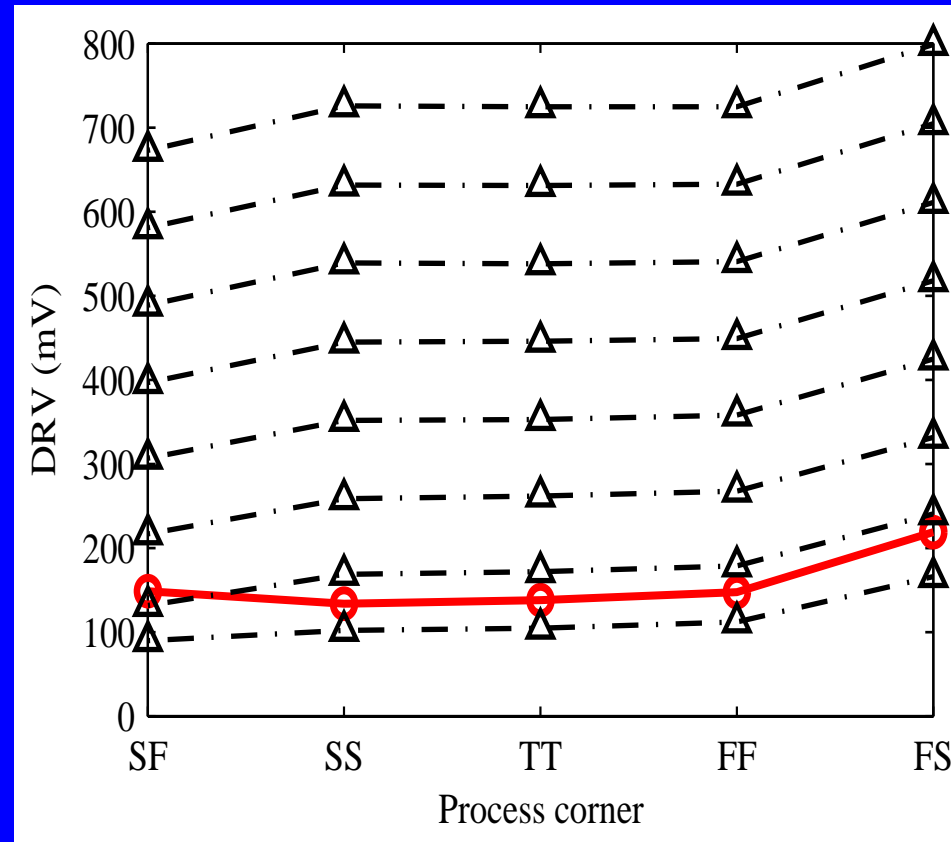
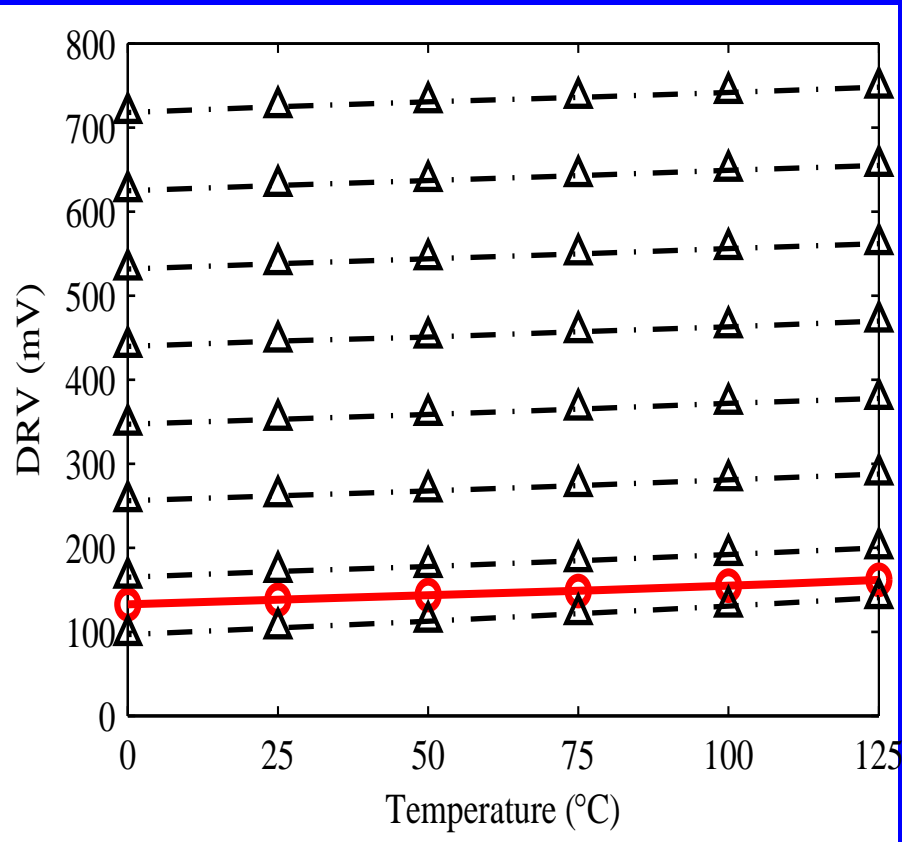
Canary set # **Don't allow to fail** **#1 #2 #3** **#4 #5 #6 #7 #8** **Allow to fail**



e.g.  $5\sigma$  (99.9999713%)  
SRAM cells will fail  
after canary set #3  
(120mV VCTRL)

# Canary Tracking Variations

- Worst DRV<sub>core</sub> (e.g. 1Kb SRAM)
- △— DRV of each canary set



- Canaries track temperature changes

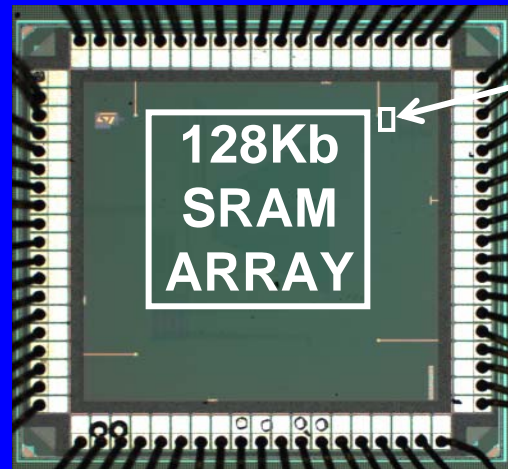
- Canaries track global process variation

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# 90nm CMOS Test Chip

- 90nm bulk, 7 metals, 1.0V VDD
- Die area: 1.51mm<sup>2</sup> x 1.51mm<sup>2</sup>
- Active circuit area
  - SRAM array (128Kb): 700x620um<sup>2</sup>
  - Canary replicas (8x3x2b): 40x70um<sup>2</sup>
  - Area overhead: **0.6%**

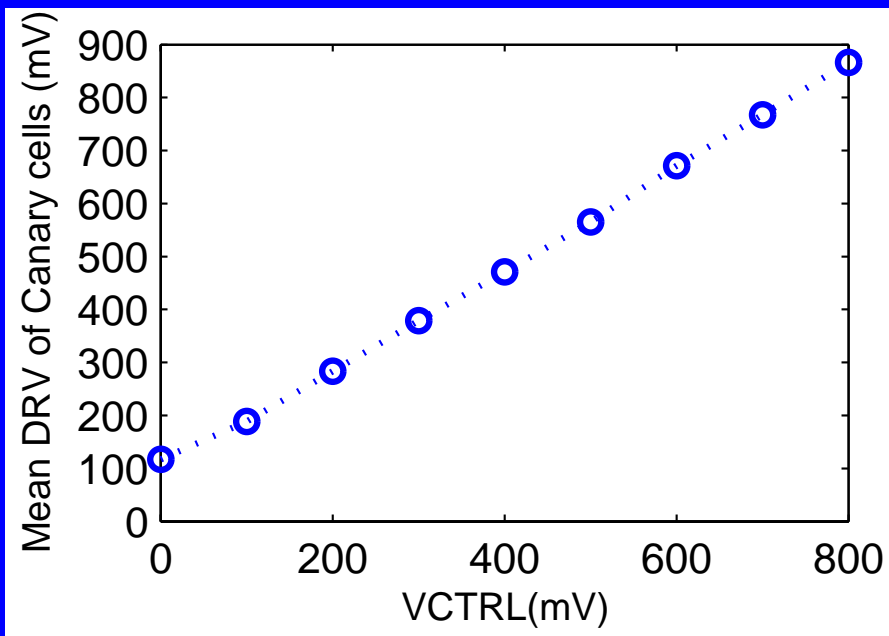


Canary Replicas

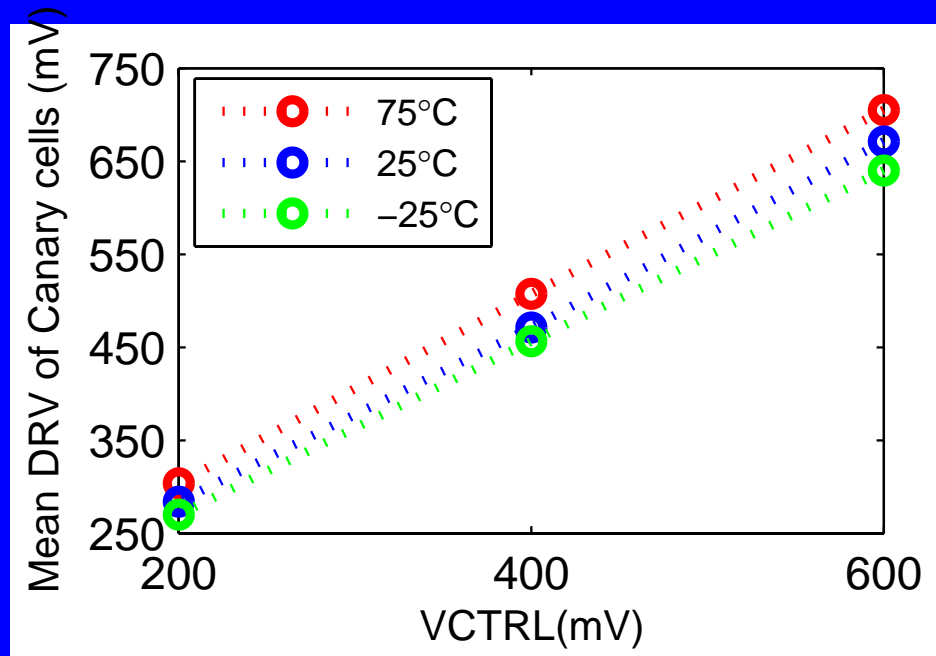


# Test Chip Measurement 1

- Measured Canary-cell DRV vs. VCTRL

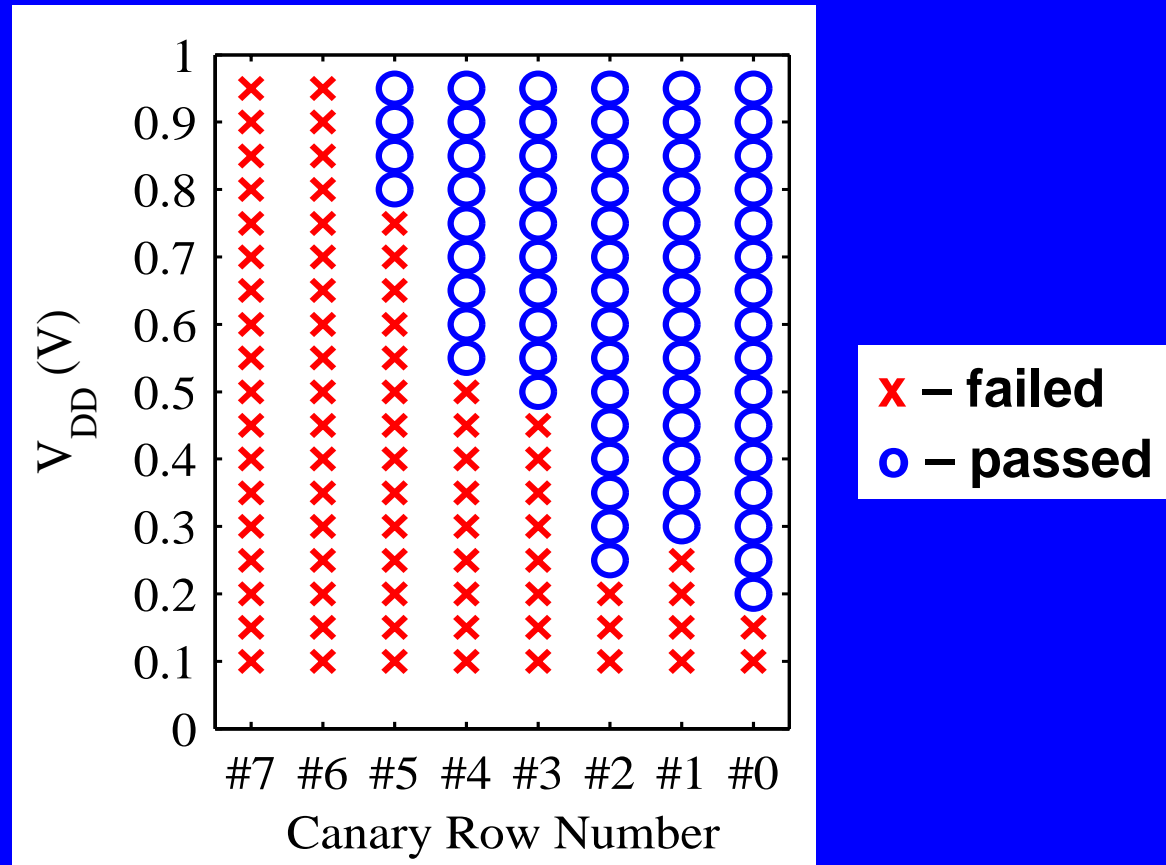


- Measured Canary-cell DRV tracks temperature variation



# Test Chip Measurement 2

- More canary sets fail with  $V_{DD}$  scaling



# Conclusion

- **New canary feedback scheme is proposed to implement aggressive  $V_{DD}$  scaling for SRAM standby leakage power reduction**
- **By controlling PMOS header, canary sets reliably fail in a continuum at higher voltages than the average of SRAM cells**
- **Canary cells can successfully track global variations**
- **Our canary scheme also allows to trade off data reliability with power savings**
- **Measurement of a 90nm test chip confirms the functions of canary scheme**